

Abstract

This invention pertains to electronic/optoelectronic devices with reduced extended defects and to a method for making it. The method includes the steps of depositing a dielectric thin film mask material on a semiconductor substrate surface; patterning the mask material to form openings therein extending to the substrate surface; growing active material in the openings; removing the mask material to form the device with reduced extended defect density; and depositing electrical contacts on the device.

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